

Features

- Low on-resistance.
- ESD Protected Gate Up to 2KV HBM
- High-speed switching.
- Drive circuits can be simple.
- Parallel use is easy.



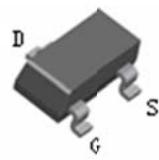
Lead-free
HF

Typical Applications

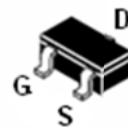
- N-channel enhancement mode effect transistor.
- Switching application.

Mechanical Data

- Case: SOT-23, SOT-323, SOT-523, DFN1006-3.
- Molding Compound, UL Flammability Classification Rating 94V-0.
- Terminals: Matte Tin Plated Leads, Solderable Per MIL-STD-202, Method 208.



2N7002H
SOT-23



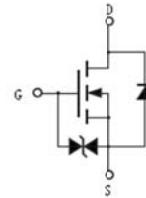
2N7002HW
SOT-323



2N7002HT
SOT-523



2N7002HL
DFN1006-3



Ordering Information

Part Number	Package	Shipping	Marking Code
2N7002H□	SOT-23	3000/Tape&Reel	7002K
2N7002HW□	SOT-323	3000/Tape&Reel	RKS
2N7002HT□	SOT-523	3000/Tape&Reel	7002K
2N7002HL□	DFN1006-3	10000/Tape&Reel	72

□: none is for Lead Free package;

"G" is for Halogen Free package.

Maximum Ratings (@T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Gate -Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	I _D	300	mA
Pulsed Drain Current ^(NOTE4)	I _{DM}	800	mA
Power Dissipation	P _D	0.35	W
		0.25	
		0.15	
		0.15	

Thermal Characteristics

Parameter		Symbol	Limits	Unit		
Thermal Resistance Junction to Ambient Air	SOT-23	$R_{\theta JA}$	357	°C/W		
	SOT-323		500			
	SOT-523		833			
	DFN1006-3		833			
Operating Junction Temperature Range		T_j	150	°C		
Storage Temperature Range		T_{STG}	-55 to +150	°C		

Electrical Characteristics (@ $T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test conditions	MIN	TYP	MAX	UNIT
OFF Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=60V, V_{GS}=0V$	-	-	1	uA
I_{GSS}	Gate-body Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	uA
ON Characteristics ^(NOTE2)						
$R_{DS(ON)}$	Static Drain-Source On-resistance	$V_{GS}=5V, I_D=0.05A$	-	1.5	3	Ω
		$V_{GS}=10V, I_D=0.5A$	-	1.45	2.5	
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Dynamic Characteristics ^(NOTE3)						
Ciss	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 20V$ $f = 1.0MHz$	-	41	-	pF
Coss	Output Capacitance		-	15	-	
Crss	Reverse Transfer Capacitance		-	4	-	
Switching Characteristics ^(NOTE3)						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=0.2A$ $V_{GS}=10V, R_G=25\Omega$ $R_L=150\Omega$	-	6	-	nS
t_r	Turn-on Rise Time		-	5	-	
$t_{d(off)}$	Turn-Off Delay Time		-	25	-	
t_f	Turn-Off Fall Time		-	15	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^(NOTE1)	$I_S=0.3A, V_{GS}=0V$	-	0.85	1.2	V
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$	-	-	0.3	A

NOTE:

- 1、 Surface Mounted on FR4 Board, $t \leq 10$ sec
- 2、 Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 3、 Guaranteed by design, not subject to production.
- 4、 Pulse width limited by maximum junction temperature.

Ratings and Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

FIG 1.OUTPUT CHARACTERISTICS

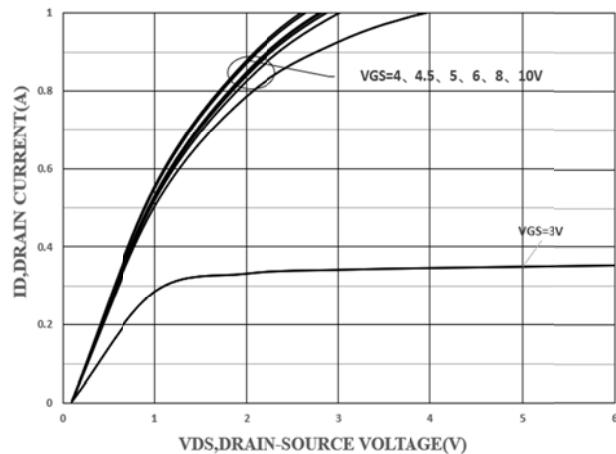


FIG 2.DRAIN-SOURCE ON RESISTANCE

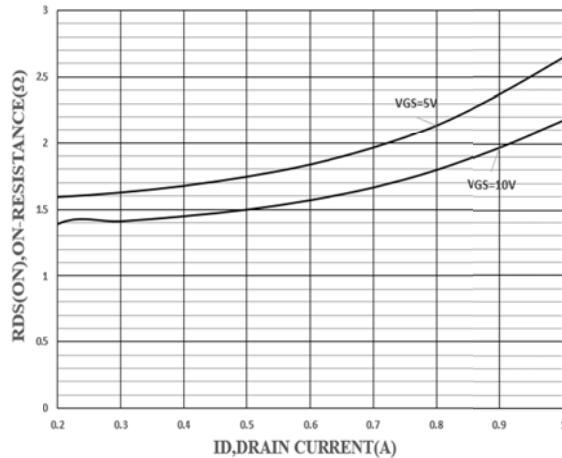


FIG 3.DRAIN-SOURCE ON RESISTANCE

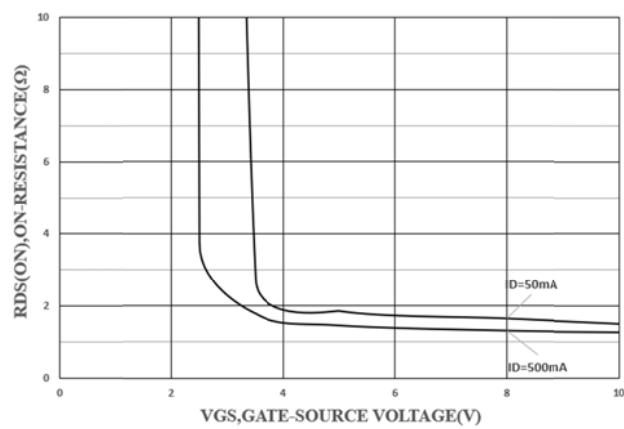


FIG 4.GATE THRESHOLD VOLTAGE

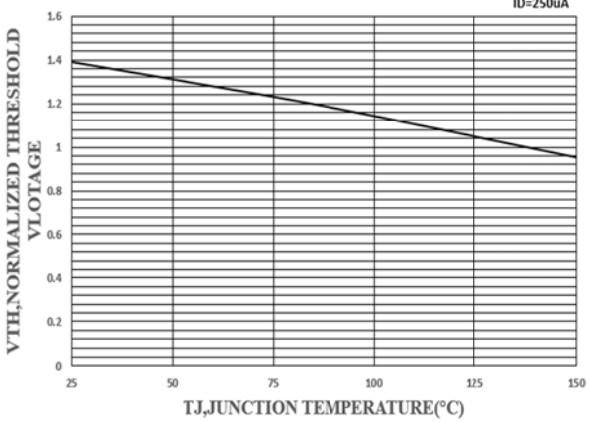


FIG 5.DRAIN-SOURCE ON RESISTANCE

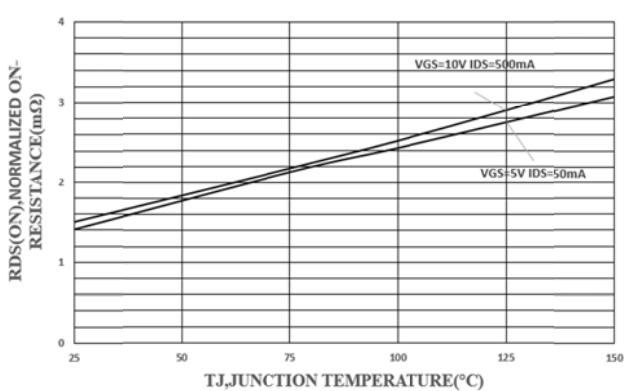
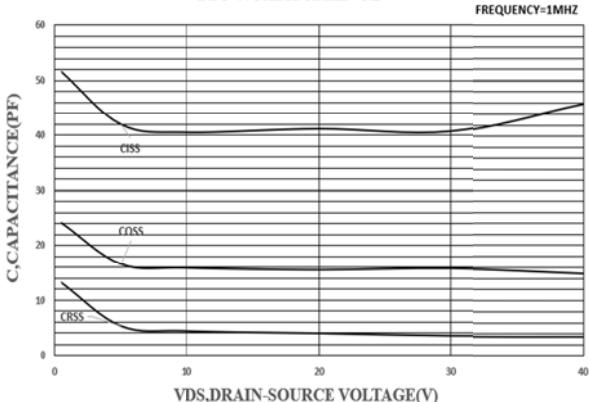
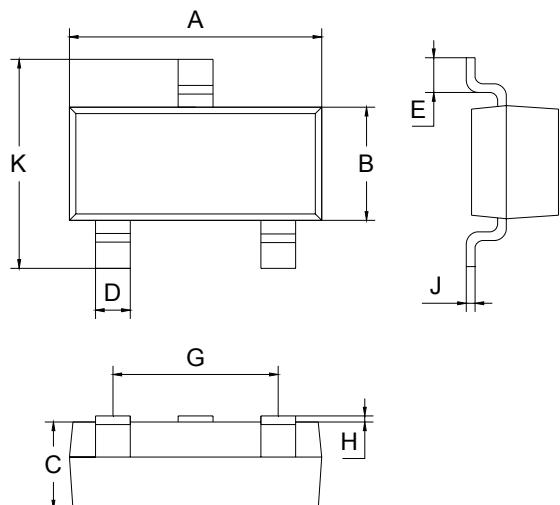
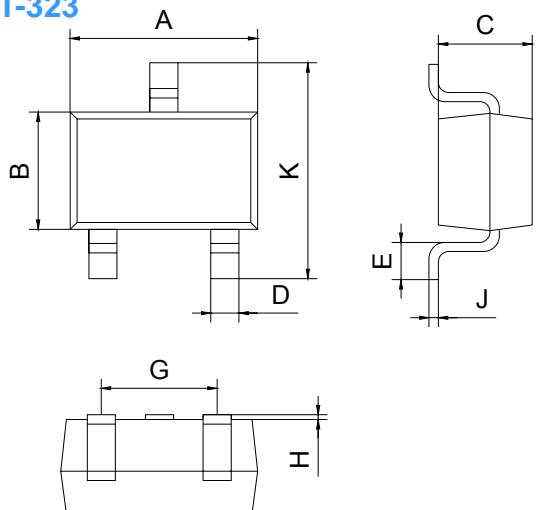


FIG 6.CAPACITANCE

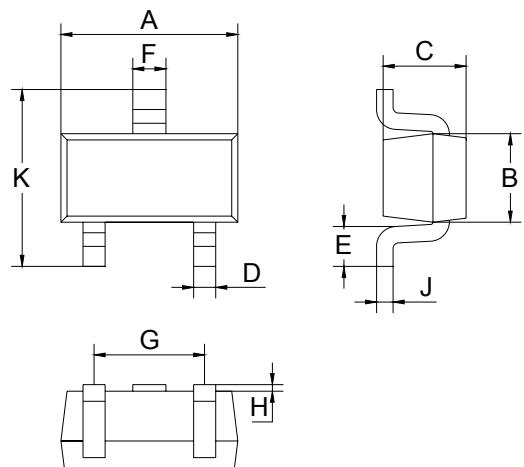


Package Outline Dimensions(unit:mm)
SOT-23


SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

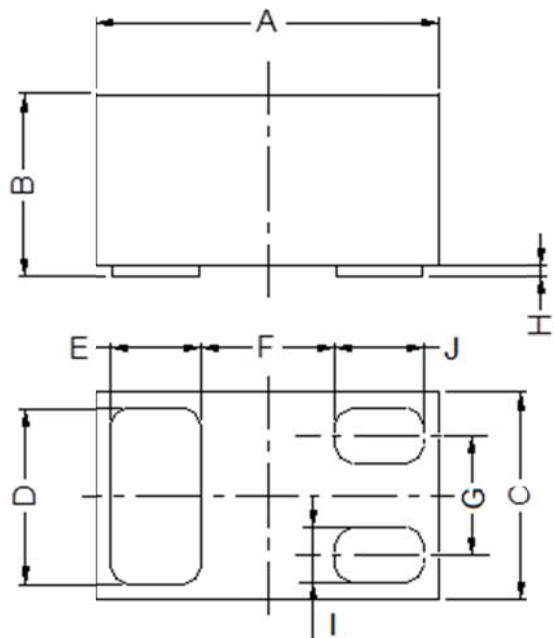
SOT-323

SOT-323

Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

SOT-523

SOT-523

Dim	Min	Max
A	1.50	1.70
B	0.75	0.85
C	0.60	0.80
D	0.15	0.30
E	0.30	0.40
F	0.25	0.40
G	0.90	1.10
H	0.02	0.10
J	0.08	0.18
K	1.45	1.75

DFN1006-3

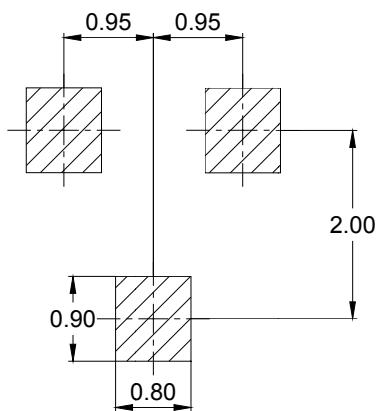


DFN1006-3			
Dim	Min	Typ	Max
A	0.95	1.00	1.075
B	0.47	0.50	0.53
C	0.55	0.60	0.675
D	0.45	0.50	0.55
E/J	0.20	0.25	0.30
F	-	0.40	-
G	-	0.35	-
H	0	0.03	0.05
I	0.10	0.15	0.20

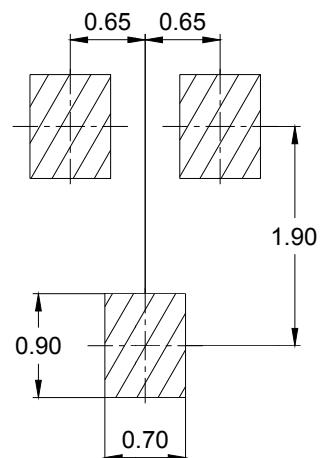
All Dimensions in mm

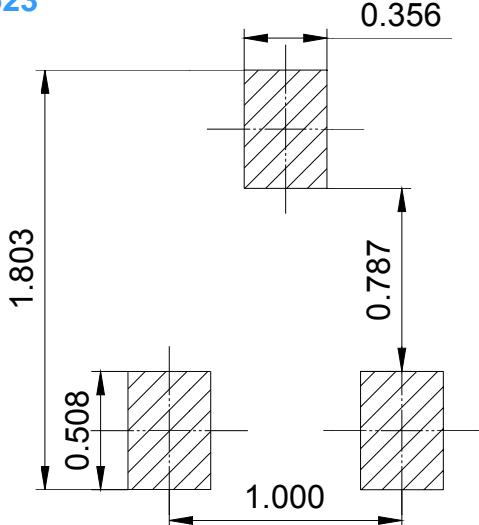
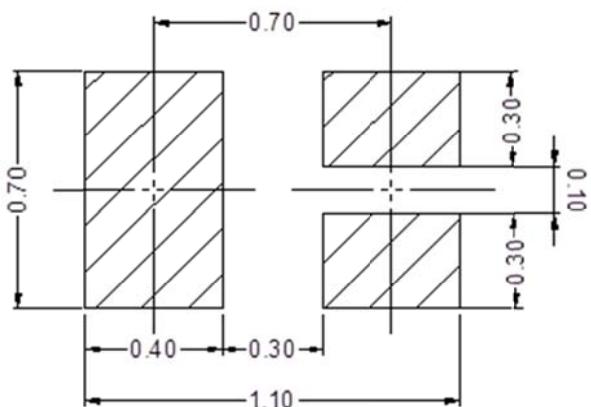
Mounting Pad Layout(unit:mm)

SOT-23



SOT-323



SOT-523

DFN1006-3

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